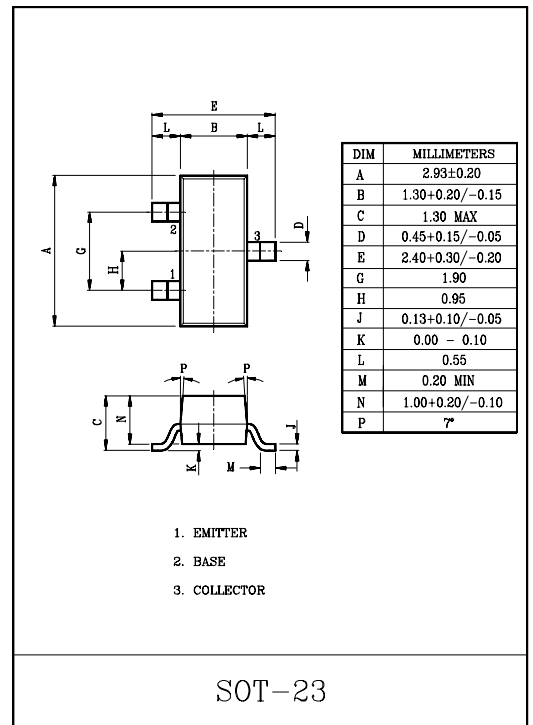


GENERAL PURPOSE APPLICATION.
DARLINGTON TRANSISTOR.

MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	MMBTA63/64	V _{CBO}	-30 V
Collector-Emitter Voltage	MMBTA63/64	V _{CES}	-30 V
Emitter-Base Voltage		V _{EBO}	-10 V
Collector Current		I _C	-500 mA
Collector Power Dissipation		P _C	350 mW
Junction Temperature		T _j	150 °C
Storage Temperature Range		T _{stg}	-55 ~ 150 °C



ELECTRICAL CHARACTERISTICS (Ta=25°C)

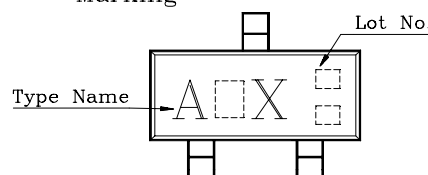
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Collector-Emitter Breakdown Voltage	V _{CES}	I _C =-0.1mA	-30	-	-	V	
Collector Cut-off Current	I _{CBO}	V _{CB} =-30V	-	-	-0.1	μA	
Emitter Cut-off Current	I _{EBO}	V _{EB} =-10V	-	-	-0.1	μA	
DC Current Gain	MMBTA63	h _{FE} (1) I _C =-10mA, V _{CE} =-5V	5,000	-	-		
	MMBTA64		10,000	-	-		
	MMBTA63	h _{FE} (2) I _C =-100mA, V _{CE} =-5V	10,000	-	-		
	MMBTA64		20,000	-	-		
Collector-Emitter Saturation Voltage	MMBTA63/64	V _{CE(sat)}	I _C =-100mA, I _B =-0.1mA	-	-	-1.5	V
Base Emitter Voltage	MMBTA63/64	V _{BE}	I _C =-100mA, V _{CE} =-5V	-	-	-2.0	V
Current Gain Bandwidth Product	MMBTA63/64	f _T	I _C =-10mA, f=100MHz V _{CE} =-5V	125	-	-	MHz

* Pulse Test : Pulse Width ≤ 300μS, Duty Cycle ≤ 2%

MARK SPEC

TYPE	MMBTA63	MMBTA64
MARK	AGX	AFX

Marking



MMBTA63/64

